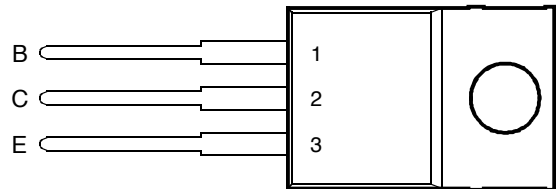


BD244, BD244A, BD244B, BD244C PNP SILICON POWER TRANSISTORS

BOURNS®

- Designed for Complementary Use with the BD243 Series
- 65 W at 25°C Case Temperature
- 6 A Continuous Collector Current
- 10 A Peak Collector Current
- Customer-Specified Selections Available

TO-220 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRACA



This series is β not recommended for new designs.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-emitter voltage ($R_{BE} = 100 \Omega$)	BD244	V_{CER}	-55	V
	BD244A		-70	
	BD244B		-90	
	BD244C		-115	
Collector-emitter voltage ($I_C = -30 \text{ mA}$)	BD244	V_{CEO}	-45	V
	BD244A		-60	
	BD244B		-80	
	BD244C		-100	
Emitter-base voltage		V_{EBO}	-5	V
Continuous collector current		I_C	-6	A
Peak collector current (see Note 1)		I_{CM}	-10	A
Continuous base current		I_B	-3	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	65	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	2	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	62.5	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	250	°C

NOTES: 1. This value applies for $t_p \leq 0.3 \text{ ms}$, duty cycle $\leq 10\%$.

2. Derate linearly to 150°C case temperature at the rate of 0.52 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20 \text{ mH}$, $I_{B(on)} = -0.4 \text{ A}$, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = -20 \text{ V}$.

PRODUCT INFORMATION

JUNE 1973 - REVISED SEPTEMBER 2002

Specifications are subject to change without notice.

electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = -30 \text{ mA}$ (see Note 5)	$I_B = 0$	BD244 BD244A BD244B BD244C	-45 -60 -80 -100			V
I_{CES} Collector-emitter cut-off current	$V_{CE} = -55 \text{ V}$ $V_{CE} = -70 \text{ V}$ $V_{CE} = -90 \text{ V}$ $V_{CE} = -115 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	BD244 BD244A BD244B BD244C			-0.4 -0.4 -0.4 -0.4	mA
I_{CEO} Collector cut-off current	$V_{CE} = -30 \text{ V}$ $V_{CE} = -60 \text{ V}$	$I_B = 0$ $I_B = 0$	BD244/244A BD244B/244C			-0.7 -0.7	mA
I_{EBO} Emitter cut-off current	$V_{EB} = -5 \text{ V}$	$I_C = 0$				-1	mA
h_{FE} Forward current transfer ratio	$V_{CE} = -4 \text{ V}$ $V_{CE} = -4 \text{ V}$	$I_C = -0.3 \text{ A}$ $I_C = -3 \text{ A}$	(see Notes 5 and 6)	30 15			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = -1 \text{ A}$	$I_C = -6 \text{ A}$	(see Notes 5 and 6)			-1.5	V
V_{BE} Base-emitter voltage	$V_{CE} = -4 \text{ V}$	$I_C = -6 \text{ A}$	(see Notes 5 and 6)			-2	V
h_{fe} Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$	$I_C = -0.5 \text{ A}$	$f = 1 \text{ kHz}$	20			
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$	$I_C = -0.5 \text{ A}$	$f = 1 \text{ MHz}$	3			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1.92	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = -1 \text{ A}$	$I_{B(on)} = -0.1 \text{ A}$	$I_{B(off)} = 0.1 \text{ A}$		0.3		μs
t_{off} Turn-off time	$V_{BE(off)} = 3.7 \text{ V}$	$R_L = 20 \Omega$	$t_p = 20 \mu\text{s}$, dc $\leq 2\%$		1		μs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN
VS
COLLECTOR CURRENT

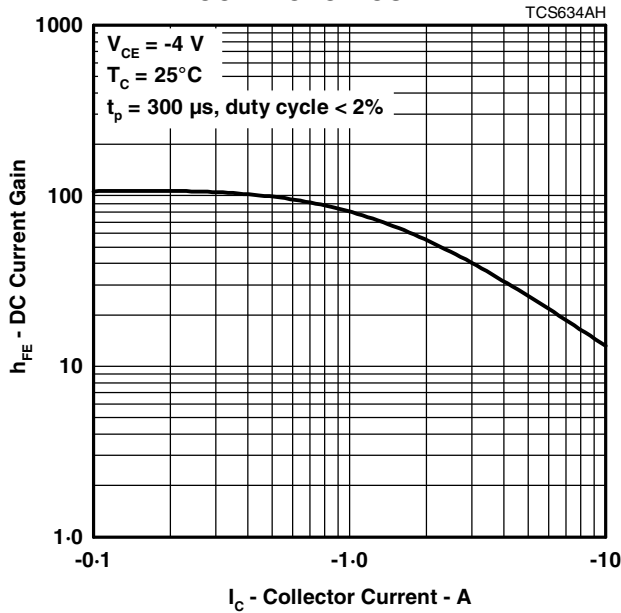


Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE
VS
BASE CURRENT

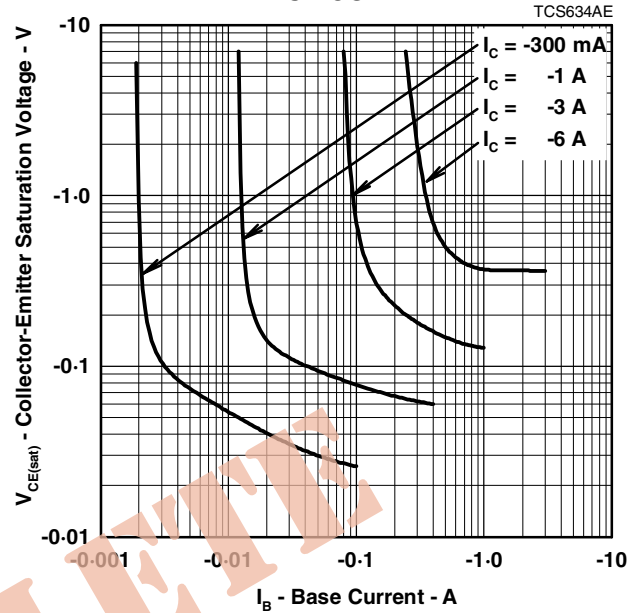


Figure 2.

BASE-EMITTER VOLTAGE
VS
COLLECTOR CURRENT

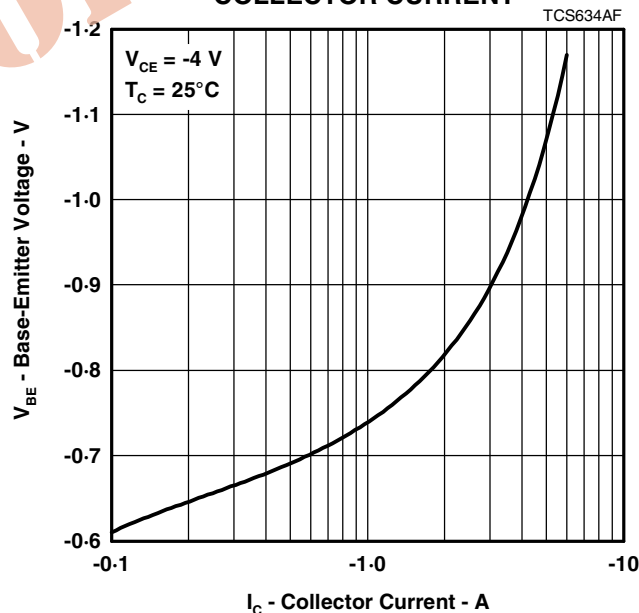


Figure 3.

PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS

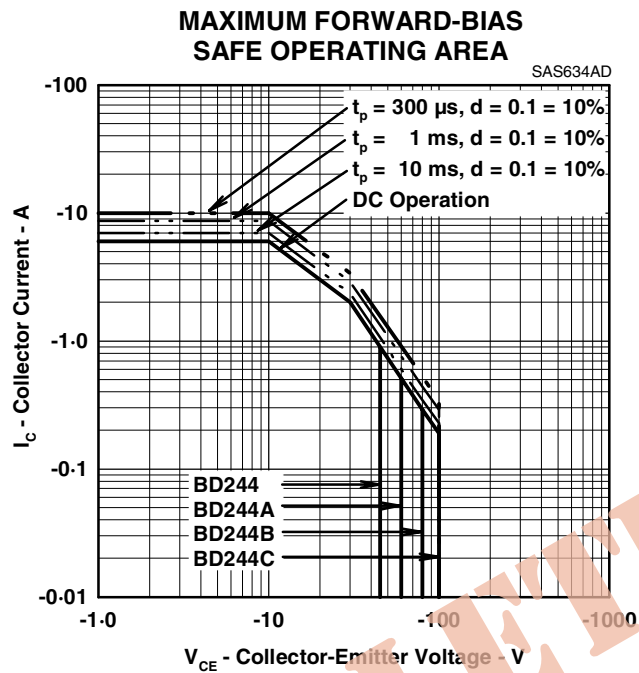


Figure 4.

THERMAL INFORMATION

**MAXIMUM POWER DISSIPATION
vs
CASE TEMPERATURE**

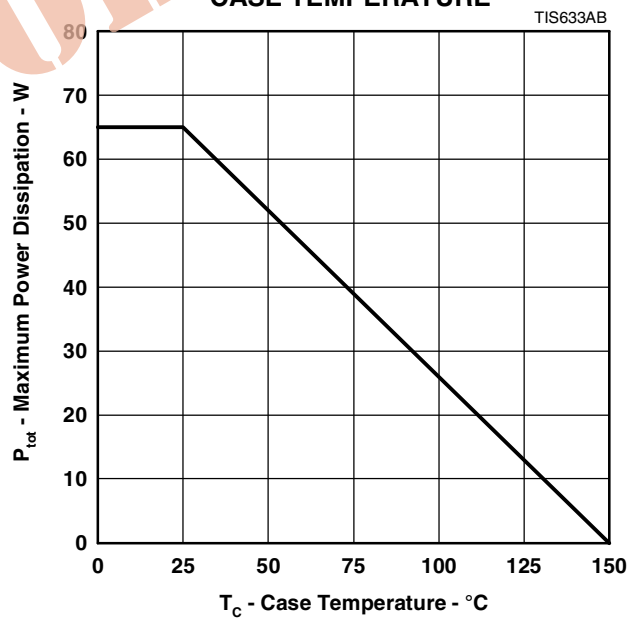


Figure 5.

PRODUCT INFORMATION